NEC

MOS INTEGRATED CIRCUIT

μPD4216100, 4217100

16 M-BIT DYNAMIC RAM
16 M-WORD BY 1-BIT, FAST PAGE MODE

Description

The μPD4216100, 4217100 are 16 777 216 words by 1 bit dynamic CMOS RAMs.
These are packed in 26-pin Plastic TSOP (II) and 26-pin Plastic SOJ.

Features

- 16 777 216 words by 1 bit organization
- Single +5.0 V±10 % power supply
- Fast page mode
- Fast access and cycle time

Part number	Power consumption Active (MAX.)	Access time (MAX.)	R/W cycle time (MIN.)	Fast page mode cycle time (MIN.)
μPD4216100-50	550 mW	50 ns	90 ns	35 ns
μPD4217100-50	660 mW			
μPD4216100-60	495 mW	60 ns	110 ns	40 ns
μPD4217100-60	605 mW			
μPD4216100-70	440 mW	70 ns	130 ns	45 ns
μPD4217100-70	550 mW			

Part number	Refresh cycle	Refresh	Power consumption at standby (MAX.)
μPD4216100	4 096 cycles/64 ms	$\overline{CAS}$ before $\overline{RAS}$ refresh, $\overline{RAS}$ only refresh, Hidden refresh	5.5 mW (CMOS level input)
μPD4217100	2 048 cycles/32 ms		

IC-2923C (Japan)

Ordering Information

Part number	Access time (MAX.)	Package	Refresh
μPD4216100G3-50	50 ns	26-pin Plastic TSOP (II) (300 mil)	$\overline{CAS}$ before $\overline{RAS}$ refresh $\overline{RAS}$ only refresh Hidden refresh
μPD4217100G3-50			
μPD4216100G3-60	60 ns		
μPD4217100G3-60			
μPD4216100G3-70	70 ns		
μPD4217100G3-70			
μPD4216100LA-50	50 ns	26-pin Plastic SOJ (300 mil)	
μPD4217100LA-50			
μPD4216100LA-60	60 ns		
μPD4217100LA-60			
μPD4216100LA-70	70 ns		
μPD4217100LA-70			

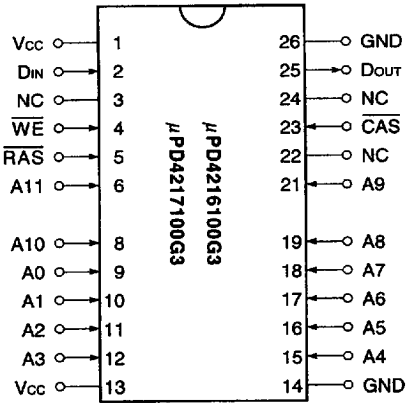
Quality Grade

Standard

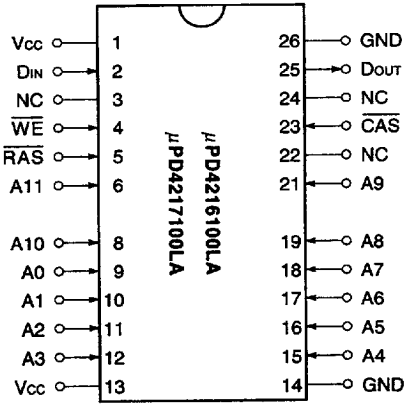
Please refer to "Quality grade on NEC Semiconductor Devices" (Document number IEI-1209) published by NEC Corporation to know the specification of quality grade on the devices and its recommended applications.

Pin Configurations (Marking Side)

26-pin Plastic TSOP (II) (300 mil)



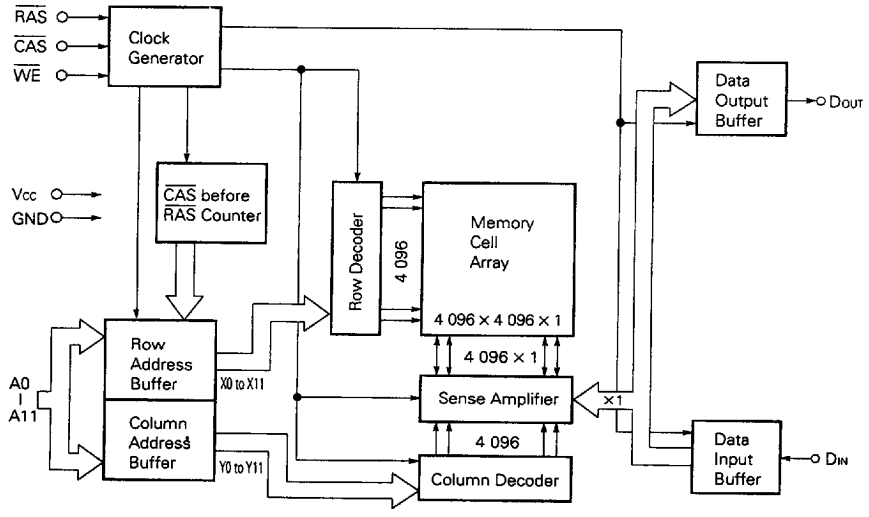
26-pin Plastic SOJ (300 mil)



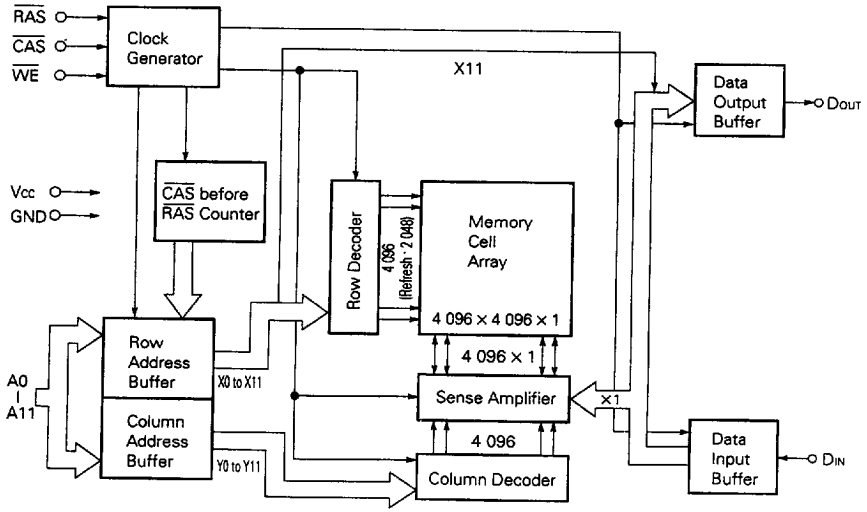
A0 to A11	: Address Inputs
DIN	: Data Input
DOUT	: Data Output
$\overline{RAS}$	: Row Address Strobe
$\overline{CAS}$	: Column Address Strobe
$\overline{WE}$	: Write Enable
Vcc	: Power Supply
GND	: Ground
NC	: No Connection

Block Diagram

[μPD4216100]



[μPD4217100]



Input/Output Pin Functions

The μPD4216100, 4217100 have input pins $\overline{RAS}$, $\overline{CAS}$, $\overline{WE}$, A0 to A11, D_{IN} and output pin D_{OUT}.

Pin name	Input/ Output	Function
$\overline{RAS}$ (Row address strobe)	Input	$\overline{RAS}$ activates the sense amplifier by latching a row address and selecting a corresponding word line. It refreshes memory cell array of one line selected by the row address. It also selects the following function. • $\overline{CAS}$ before $\overline{RAS}$ refresh
$\overline{CAS}$ (Column address strobe)		$\overline{CAS}$ activates data input/output circuit by latching column address and selecting a digit line connected with the sense amplifier.
A0 to A11 (Address inputs)		Address bus. Input total 24-bit of address signal, upper 12-bit and lower 12-bit in sequence (address multiplex method). Therefore, one word is selected from 16 777 216-word by 1-bit memory cell array. In actual operation, latch row address by specifying row address and activating $\overline{RAS}$. Then, switch the address bus to column address and activate $\overline{CAS}$. Each address is taken into the device when $\overline{RAS}$ and $\overline{CAS}$ are activated. Therefore, the address input setup time (t_{ASR}, t_{ASC}) and hold time (t_{RAH}, t_{CAH}) are specified for the activation of $\overline{RAS}$ and $\overline{CAS}$.
$\overline{WE}$ (Write enable)		Write control signal. Write operation is executed by activating $\overline{RAS}$, $\overline{CAS}$ and $\overline{WE}$.
D_{IN} (Data input)		Data bus. D_{IN} is used to input data.
D_{OUT} (Data output)	Output	Data bus. D_{OUT} is used to output data.

Electrical Specifications

- All voltages are referenced to GND.
- After power up, wait more than 100 μs and then, execute eight $\overline{CAS}$ before $\overline{RAS}$ or $\overline{RAS}$ only refresh cycles as dummy cycles to initialize internal circuit.

Absolute Maximum Ratings

Parameter	Symbol	Condition	Rating	Unit
Voltage on any pin relative to GND	V_T		−1.0 to +7.0	V
Supply voltage	V_{CC}		−1.0 to +7.0	V
Output current	I_O		50	mA
Power dissipation	P_D		1	W
Operating temperature	T_{opt}		0 to +70	°C
Storage temperature	T_{stg}		−55 to +125	°C

Caution Exposing the device to stress above those listed in Absolute Maximum Ratings could cause permanent damage. The device is not meant to be operated under conditions outside the limits described in the operational section of this specification. Exposure to Absolute Maximum Rating conditions for extended periods may affect device reliability.

Recommended Operating Conditions

Parameter	Symbol	Condition	MIN.	TYP.	MAX.	Unit
Supply voltage	V_{CC}		4.5	5.0	5.5	V
High level input voltage	V_{IH}		2.4		V_{CC} + 1.0	V
Low level input voltage	V_{IL}		−1.0		+0.8	V
Ambient temperature	T_a		0		70	°C

Capacitance (T_a = +25 °C, f = 1 MHz)

Parameter	Symbol	Condition	MIN.	TYP.	MAX.	Unit
Input capacitance	C_{I1}	A0 to A11, D_{IN}			5	pF
	C_{I2}	$\overline{RAS}$, $\overline{CAS}$, $\overline{WE}$			7	pF
Data Output capacitance	C_O	D_{OUT}			7	pF

DC Characteristics (Recommended Operating Conditions unless otherwise noted)

[μPD4216100]

Parameter		Symbol	Test condition		MIN.	MAX.	Unit	Notes
Operating current		I_{CC1}	$\overline{RAS}$, $\overline{CAS}$ Cycling $t_{RC} = t_{RC}$ (MIN.) I_O = 0 mA	t_{RAC} = 50 ns		100	mA	1, 2, 3
				t_{RAC} = 60 ns		90		
				t_{RAC} = 70 ns		80		
				t_{RAC} = 80 ns		70		
Standby current		I_{CC2}					mA	
	μPD4216100		$\overline{RAS}$, $\overline{CAS} \geqq V_{IH}$ (MIN.)	I_O = 0 mA		2		
			$\overline{RAS}$, $\overline{CAS} \geqq V_{CC} - 0.2$ V	I_O = 0 mA		1		
$\overline{RAS}$ only refresh current		I_{CC3}	$\overline{RAS}$ Cycling $\overline{CAS} \geqq V_{IH}$ (MIN.) $t_{RC} = t_{RC}$ (MIN.) I_O = 0 mA	t_{RAC} = 50 ns		100	mA	1, 2, 3, 4
				t_{RAC} = 60 ns		90		
				t_{RAC} = 70 ns		80		
				t_{RAC} = 80 ns		70		
Operating current (Fast page mode)		I_{CC4}	$\overline{RAS} \leqq V_{IL}$ (MAX.) $\overline{CAS}$ Cycling $t_{PC} = t_{PC}$ (MIN.) I_O = 0 mA	t_{RAC} = 50 ns		80	mA	1, 2, 5
				t_{RAC} = 60 ns		70		
				t_{RAC} = 70 ns		60		
				t_{RAC} = 80 ns		50		
$\overline{CAS}$ before $\overline{RAS}$ refresh current		I_{CC5}	$\overline{RAS}$ Cycling $t_{RC} = t_{RC}$ (MIN.) I_O = 0 mA	t_{RAC} = 50 ns		100	mA	1, 2
				t_{RAC} = 60 ns		90		
				t_{RAC} = 70 ns		80		
				t_{RAC} = 80 ns		70		
$\overline{CAS}$ before $\overline{RAS}$ long refresh current (4 096 cycles / 128 ms, only for μPD42S16100)		I_{CC6}	$\overline{CAS}$ before $\overline{RAS}$ refresh : 4 096 cycles/128 ms $\overline{RAS}$, $\overline{CAS}$: 0 V ≦ V_{IL} ≦ 0.2 V $V_{CC}-0.2V \leqq V_{IH} \leqq V_{IH(MAX)}$ Standby : $\overline{RAS} \geqq V_{CC} - 0.2$ V Address : Don't care $\overline{WE}$: V_{IH} I_O = 0 mA	$t_{RAS} \leqq 300$ ns		450	μA	1, 2
				$t_{RAS} \leqq 1$ μs		600		
Input leakage current		$I_{I(L)}$	V_I = 0 to 5.5 V all other pins not under test = 0 V		−10	+10	μA	
Output leakage current		$I_{O(L)}$	V_O = 0 to 5.5 V Output is disabled (Hi-Z)		−10	+10	μA	
High level output voltage		V_{OH}	I_O = −5.0 mA		2.4		V	
Low level output voltage		V_{OL}	I_O = +4.2 mA			0.4	V	

[μPD4217100]

Parameter		Symbol	Test condition		MIN.	MAX.	Unit	Notes
Operating current		I_{CC1}	$\overline{RAS}$, $\overline{CAS}$ Cycling $t_{RC} = t_{RC}$ (MIN.) I_O = 0 mA	t_{RAC} = 50 ns		120	mA	1, 2, 3
				t_{RAC} = 60 ns		110		
				t_{RAC} = 70 ns		100		
				t_{RAC} = 80 ns		90		
Standby current		I_{CC2}					mA	
	μPD4217100							
			$\overline{RAS}$, $\overline{CAS} \geqq V_{IH}$ (MIN.)	I_O = 0 mA		2		
			$\overline{RAS}$, $\overline{CAS} \geqq V_{CC} - 0.2$ V	I_O = 0 mA		1		
$\overline{RAS}$ only refresh current		I_{CC3}	$\overline{RAS}$ Cycling $\overline{CAS} \geqq V_{IH}$ (MIN.) $t_{RC} = t_{RC}$ (MIN.) I_O = 0 mA	t_{RAC} = 50 ns		120	mA	1, 2, 3, 4
				t_{RAC} = 60 ns		110		
				t_{RAC} = 70 ns		100		
				t_{RAC} = 80 ns		90		
Operating current (Fast page mode)		I_{CC4}	$\overline{RAS} \leqq V_{IL}$ (MAX.) $\overline{CAS}$ Cycling $t_{PC} = t_{PC}$ (MIN.) I_O = 0 mA	t_{RAC} = 50 ns		80	mA	1, 2, 5
				t_{RAC} = 60 ns		70		
				t_{RAC} = 70 ns		60		
				t_{RAC} = 80 ns		50		
$\overline{CAS}$ before $\overline{RAS}$ refresh current		I_{CC5}	$\overline{RAS}$ Cycling $t_{RC} = t_{RC}$ (MIN.) I_O = 0 mA	t_{RAC} = 50 ns		120	mA	1, 2
				t_{RAC} = 60 ns		110		
				t_{RAC} = 70 ns		100		
				t_{RAC} = 80 ns		90		
Input leakage current		$I_{I(L)}$	V_I = 0 to 5.5 V all other pins not under test = 0 V		−10	+10	μA	
Output leakage current		$I_{O(L)}$	V_O = 0 to 5.5 V Output is disabled (Hi-Z)		−10	+10	μA	
High level output voltage		V_{OH}	I_O = −5.0 mA		2.4		V	
Low level output voltage		V_{OL}	I_O = +4.2 mA			0.4	V	

Notes 1. I_{CC1}, I_{CC3}, I_{CC4}, I_{CC5}, I_{CC6} depend on cycle rates (t_{RC} and t_{PC}).

2. Specified values are obtained with outputs unloaded.

3. I_{CC1} and I_{CC3} are measured assuming that address can be changed once or less during $\overline{RAS} \leqq V_{IL\,(MAX.)}$ and $\overline{CAS} \geqq V_{IH\,(MIN.)}$.

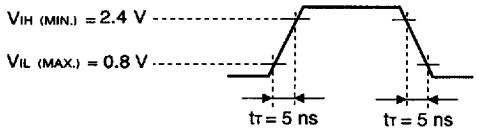
4. I_{CC3} is measured assuming that all column address inputs are held at either high or low.

5. I_{CC4} is measured assuming that all column address inputs are switched only once during each fast page cycle.

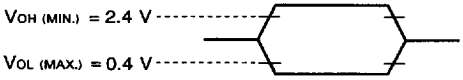
AC Characteristics (Recommended Operating Conditions unless otherwise noted)

AC Characteristics Test Conditions

(1) Input timing specification



(2) Output timing specification



(3) Loading conditions are 100 pF + 2 TTLs.

Common to Read, Write, Read Modify Write Cycle

Parameter		Symbol	tRAC = 50 ns		tRAC = 60 ns		tRAC = 70 ns		Unit	Notes
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.		
Read / Write Cycle Time		tRC	90	–	110	–	130	–	ns	
$\overline{RAS}$ Precharge Time		tRP	30	–	40	–	50	–	ns	
$\overline{CAS}$ Precharge Time		tCPN	8	–	10	–	10	–	ns	
$\overline{RAS}$ Pulse Width		tRAS	50	10 000	60	10 000	70	10 000	ns	
$\overline{CAS}$ Pulse Width		tCAS	13	10 000	15	10 000	18	10 000	ns	
$\overline{RAS}$ Hold Time		tRSH	13	–	15	–	18	–	ns	
$\overline{CAS}$ Hold Time		tCSH	50	–	60	–	70	–	ns	
$\overline{RAS}$ to $\overline{CAS}$ Delay Time		tRCD	18	32	20	40	20	50	ns	1
$\overline{RAS}$ to Column Address Delay Time		tRAD	13	25	15	30	15	35	ns	1
$\overline{CAS}$ to $\overline{RAS}$ Precharge Time		tCRP	5	–	5	–	5	–	ns	2
Row Address Setup Time		tASR	0	–	0	–	0	–	ns	
Row Address Hold Time		tRAH	8	–	10	–	10	–	ns	
Column Address Setup Time		tASC	0	–	0	–	0	–	ns	
Column Address Hold Time		tCAH	13	–	15	–	15	–	ns	
$\overline{CAS}$ to Data Setup Time		tCLZ	0	–	0	–	0	–	ns	
Transition Time (Rise and Fall)		tT	3	50	3	50	3	50	ns	
Refresh Time		tREF							ms	
	μPD4216100		–	64	–	64	–	64		
	μPD4217100		–	32	–	32	–	32		

Notes 1. For read cycles, access time is defined as follows:

Input Conditions	Access Time	Access Time from $\overline{RAS}$
$t_{RAD} \leqq t_{RAD(MAX.)}$ and $t_{RCD} \leqq t_{RCD(MAX.)}$	$t_{RAC(MAX.)}$	$t_{RAC(MAX.)}$
$t_{RAD} > t_{RAD(MAX.)}$ and $t_{RCD} \leqq t_{RCD(MAX.)}$	$t_{AA(MAX.)}$	$t_{RAD} + t_{AA(MAX.)}$
$t_{RCD} > t_{RCD(MAX.)}$	$t_{CAC(MAX.)}$	$t_{RCD} + t_{CAC(MAX.)}$

$t_{RAD(MAX.)}$ and $t_{RCD(MAX.)}$ are specified as reference points only ; they are not restrictive operating parameters. They are used to determine which access time (t_{RAC}, t_{AA} or t_{CAC}) is to be used for finding out when output data will be available. Therefore, the input conditions $t_{RAD} \geqq t_{RAD(MAX.)}$ and $t_{RCD} \geqq t_{RCD(MAX.)}$ will not cause any operation problems.

2. $t_{CRP(MIN.)}$ requirement is applied to $\overline{RAS}$, $\overline{CAS}$ cycles preceded by any cycle.

Read Cycle

Parameter	Symbol	t_{RAC} = 50 ns		t_{RAC} = 60 ns		t_{RAC} = 70 ns		Unit	Notes
		MIN.	MAX.	MIN.	MAX.	MIN.	MAX.		
Access Time from $\overline{RAS}$	t_{RAC}	–	50	–	60	–	70	ns	1
Access Time from $\overline{CAS}$	t_{CAC}	–	13	–	15	–	18	ns	1
Access Time from Column Address	t_{AA}	–	25	–	30	–	35	ns	1
Column Address Lead Time Referenced to $\overline{RAS}$	t_{RAL}	25	–	30	–	35	–	ns	
Read Command Setup Time	t_{RCS}	0	–	0	–	0	–	ns	
Read Command Hold Time Referenced to $\overline{RAS}$	t_{RRH}	0	–	0	–	0	–	ns	2
Read Command Hold Time Referenced to $\overline{CAS}$	t_{RCH}	0	–	0	–	0	–	ns	2
Output Buffer Turn-off Delay Time from $\overline{CAS}$	t_{OFF}	0	10	0	15	0	15	ns	3

Notes 1. For read cycles, access time is defined as follows:

Input Conditions	Access Time	Access Time from $\overline{RAS}$
$t_{RAD} \leqq t_{RAD(MAX.)}$ and $t_{RCD} \leqq t_{RCD(MAX.)}$	$t_{RAC(MAX.)}$	$t_{RAC(MAX.)}$
$t_{RAD} > t_{RAD(MAX.)}$ and $t_{RCD} \leqq t_{RCD(MAX.)}$	$t_{AA(MAX.)}$	$t_{RAD} + t_{AA(MAX.)}$
$t_{RCD} > t_{RCD(MAX.)}$	$t_{CAC(MAX.)}$	$t_{RCD} + t_{CAC(MAX.)}$

$t_{RAD(MAX.)}$ and $t_{RCD(MAX.)}$ are specified as reference points only ; they are not restrictive operating parameters. They are used to determine which access time (t_{RAC}, t_{AA} or t_{CAC}) is to be used for finding out when output data will be available. Therefore, the input conditions $t_{RAD} \geqq t_{RAD(MAX.)}$ and $t_{RCD} \geqq t_{RCD(MAX.)}$ will not cause any operation problems.

2. Either $t_{RCH(MIN.)}$ or $t_{RRH(MIN.)}$ should be met in read cycles.
3. $t_{OFF(MAX.)}$ defines the time when the output achieves the condition of Hi - Z and is not referenced to V_{OH} or V_{OL}.

Write Cycle

Parameter	Symbol	t_{RAC} = 50 ns		t_{RAC} = 60 ns		t_{RAC} = 70 ns		Unit	Notes
		MIN.	MAX.	MIN.	MAX.	MIN.	MAX.		
$\overline{WE}$ Hold Time Referenced to $\overline{CAS}$	t_{WCH}	8	–	10	–	10	–	ns	1
$\overline{WE}$ Pulse Width	t_{WP}	8	–	10	–	10	–	ns	1
$\overline{WE}$ Lead Time Referenced to $\overline{RAS}$	t_{RWL}	18	–	20	–	20	–	ns	
$\overline{WE}$ Lead Time Referenced to $\overline{CAS}$	t_{CWL}	13	–	15	–	15	–	ns	
$\overline{WE}$ Setup Time	t_{WCS}	0	–	0	–	0	–	ns	2
Data-in Setup Time	t_{DS}	0	–	0	–	0	–	ns	3
Data-in Hold Time	t_{DH}	10	–	10	–	15	–	ns	3

Notes 1. $t_{WP(MIN.)}$ is applied to late write cycles or read modify write cycles. In early write cycles, $t_{WCH(MIN.)}$ should be met.

2. If $t_{WCS} \geqq t_{WCS(MIN.)}$, the cycle is an early write cycle and the data out will remain Hi - Z through the entire cycle.

3. $t_{DS(MIN.)}$ and $t_{DH(MIN.)}$ are referenced to the $\overline{CAS}$ falling edge in early write cycles. In late write cycles and read modify write cycles, they are referenced to the $\overline{WE}$ falling edge.

Read Modify Write Cycle

Parameter	Symbol	t_{RAC} = 50 ns		t_{RAC} = 60 ns		t_{RAC} = 70 ns		Unit	Note
		MIN.	MAX.	MIN.	MAX.	MIN.	MAX.		
Read Modify Write Cycle Time	t_{RWC}	113	–	135	–	155	–	ns	
$\overline{RAS}$ to $\overline{WE}$ Delay Time	t_{RWD}	50	–	60	–	70	–	ns	1
$\overline{CAS}$ to $\overline{WE}$ Delay Time	t_{CWD}	13	–	15	–	18	–	ns	1
Column Address to $\overline{WE}$ Delay Time	t_{AWD}	25	–	30	–	35	–	ns	1

Note 1. If $t_{WCS} \geqq t_{WCS\,(MIN.)}$, the cycle is an early write cycle and the data out will remain Hi - Z through the entire cycle. If $t_{RWD} \geqq t_{RWD\,(MIN.)}$, $t_{CWD} \geqq t_{CWD\,(MIN.)}$, $t_{AWD} \geqq t_{AWD\,(MIN.)}$ and $t_{CPWD} \geqq t_{CPWD\,(MIN.)}$, the cycle is a read modify write cycle and the data out will contain data read from the selected cell. If neither of the above conditions is met, the state of the data out is indeterminate.

Fast Page Mode

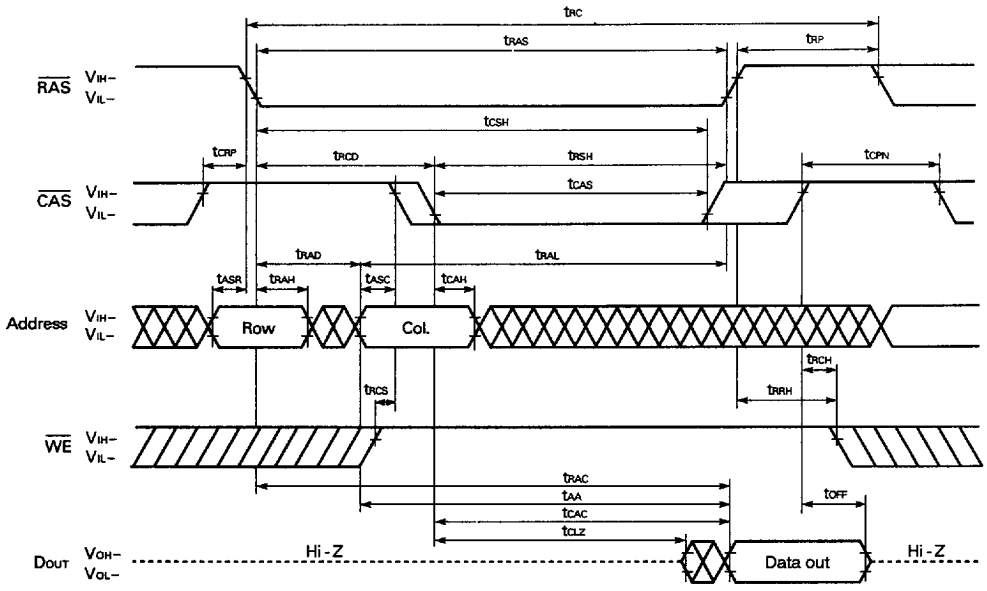
Parameter	Symbol	t_{RAC} = 50 ns		t_{RAC} = 60 ns		t_{RAC} = 70 ns		Unit	Note
		MIN.	MAX.	MIN.	MAX.	MIN.	MAX.		
Fast Page Mode Cycle Time	t_{PC}	35	–	40	–	45	–	ns	
Access Time from $\overline{CAS}$ Precharge	t_{ACP}	–	30	–	35	–	40	ns	
$\overline{RAS}$ Pulse Width	t_{RASP}	50	125 000	60	125 000	70	125 000	ns	
$\overline{CAS}$ Precharge Time	t_{CP}	8	–	10	–	10	–	ns	
$\overline{RAS}$ Hold Time from $\overline{CAS}$ Precharge	t_{RHCP}	30	–	35	–	40	–	ns	
Read Modify Write Cycle Time	t_{PRWC}	55	–	60	–	65	–	ns	
$\overline{CAS}$ Precharge to $\overline{WE}$ Delay Time	t_{CPWD}	50	–	58	–	65	–	ns	1

Note 1. If $t_{WCS} \geqq t_{WCS(MIN.)}$, the cycle is an early write cycle and the data out will remain Hi - Z through the entire cycle. If $t_{RWD} \geqq t_{RWD(MIN.)}$, $t_{CWD} \geqq t_{CWD(MIN.)}$, $t_{AWD} \geqq t_{AWD(MIN.)}$ and $t_{CPWD} \geqq t_{CPWD(MIN.)}$, the cycle is a read modify write cycle and the data out will contain data read from the selected cell. If neither of the above conditions is met, the state of the data out is indeterminate.

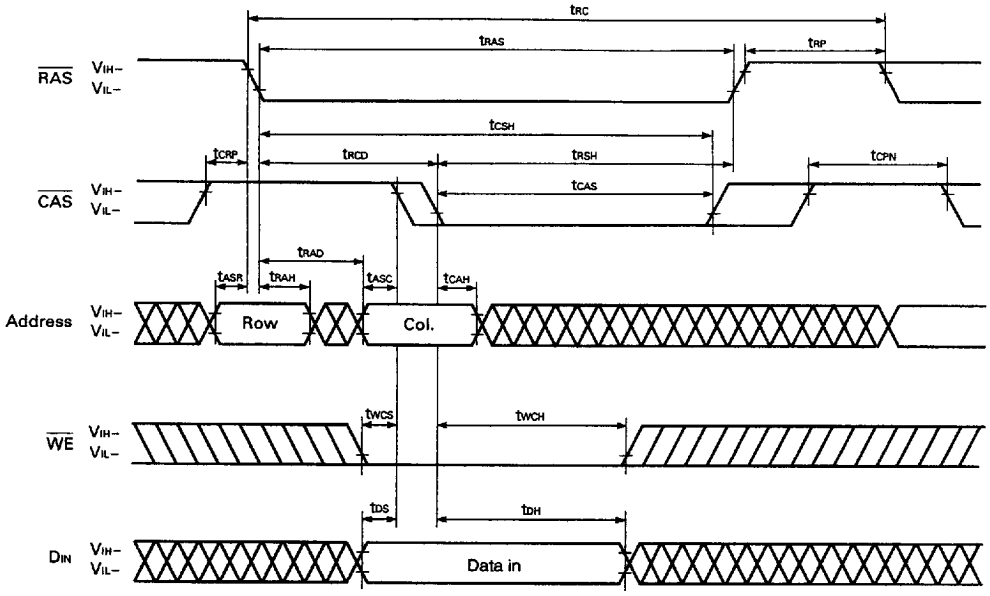
Refresh Cycle

Parameter	Symbol	t_{RAC} = 50 ns		t_{RAC} = 60 ns		t_{RAC} = 70 ns		Unit	Note
		MIN.	MAX.	MIN.	MAX.	MIN.	MAX.		
$\overline{CAS}$ Setup Time	t_{CSR}	5	–	5	–	5	–	ns	
$\overline{CAS}$ Hold Time ($\overline{CAS}$ before $\overline{RAS}$ Refresh)	t_{CHR}	10	–	10	–	10	–	ns	
$\overline{RAS}$ Precharge $\overline{CAS}$ Hold Time	t_{RPC}	5	–	5	–	5	–	ns	
$\overline{WE}$ Setup Time	t_{WSR}	10	–	10	–	10	–	ns	
$\overline{WE}$ Hold Time	t_{WHR}	15	–	15	–	15	–	ns	

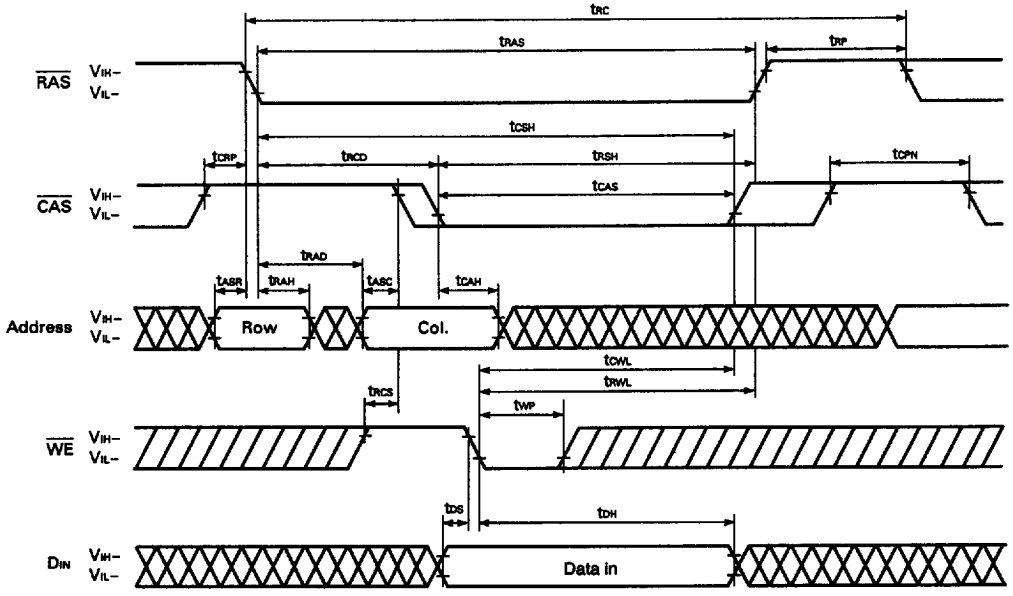
Read Cycle



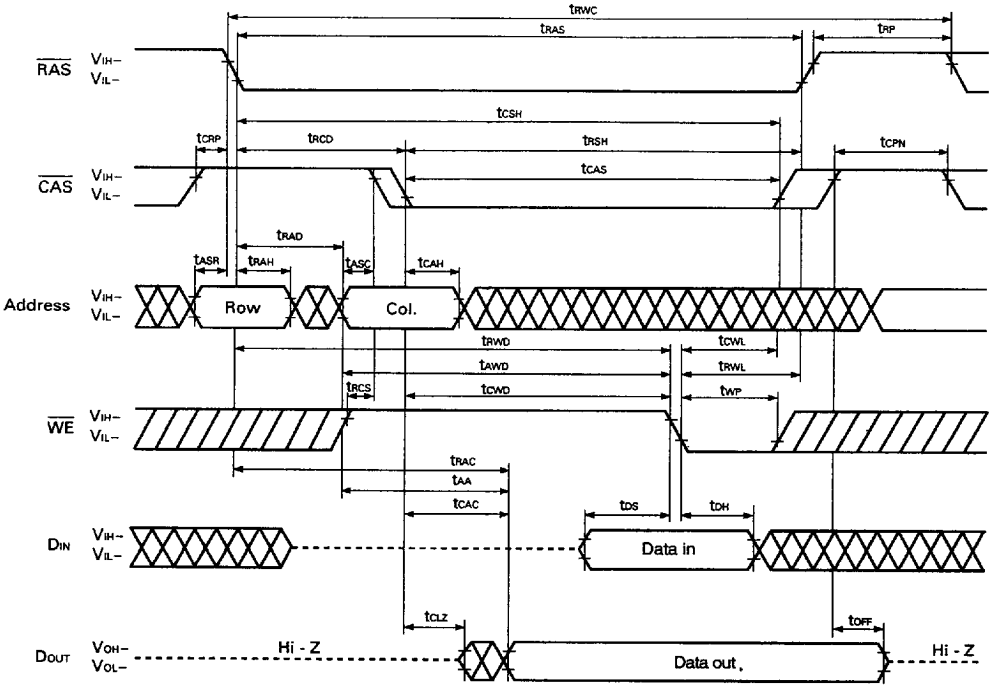
Early Write Cycle



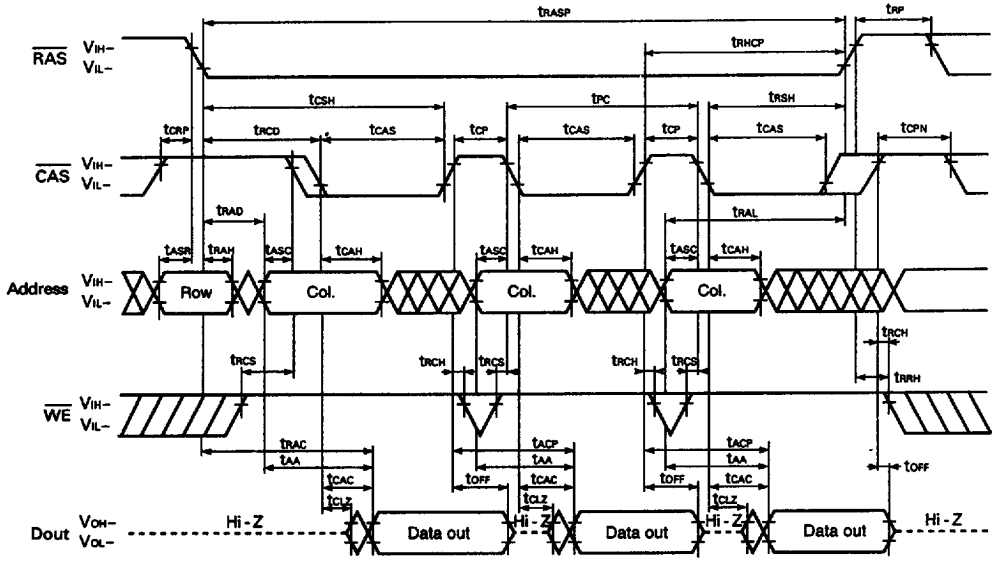
Late Write Cycle



Read Modify Write Cycle

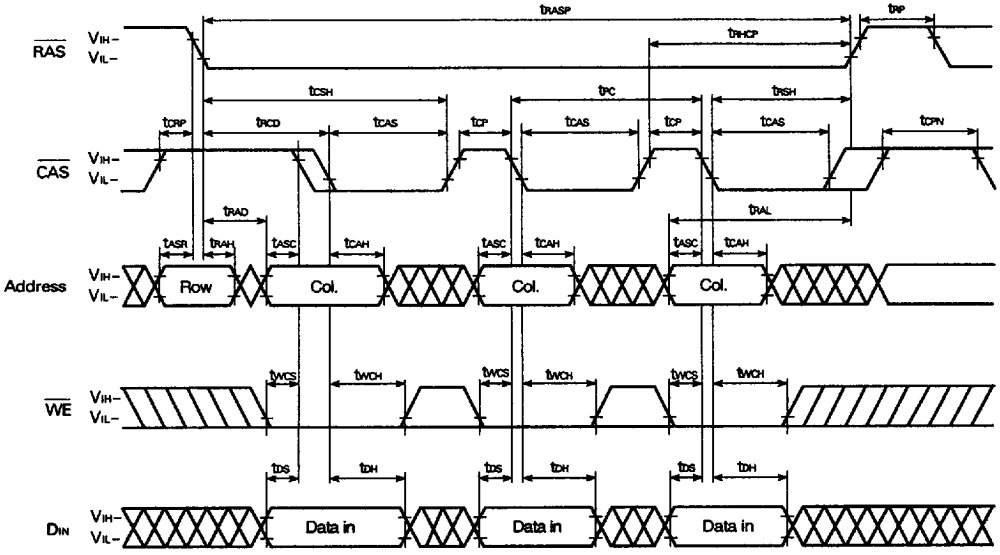


Fast Page Mode Read Cycle



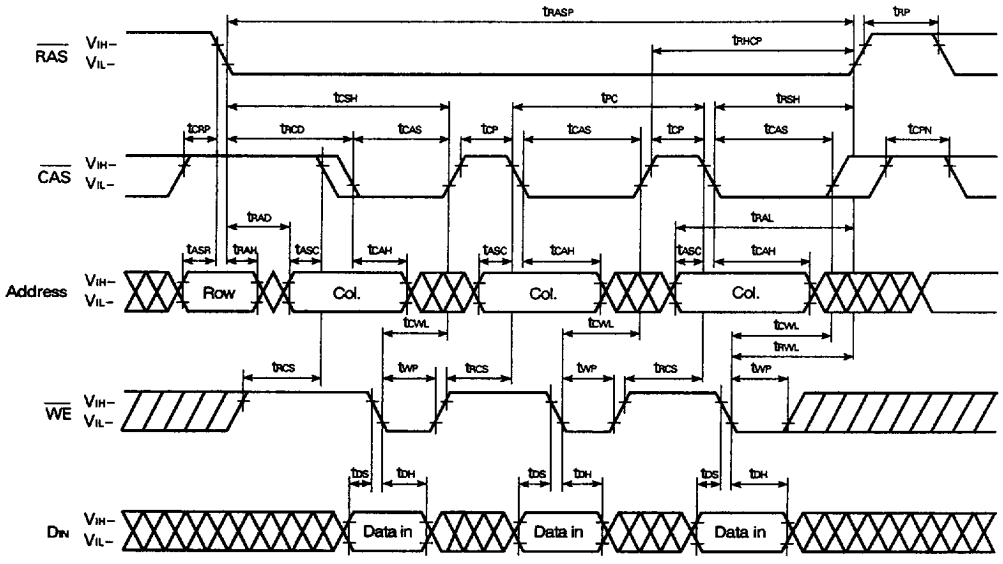
Remark In the fast page mode, read, write and read modify write cycles are available for each of the consecutive $\overline{CAS}$ cycles within the same $\overline{RAS}$ cycle.

Fast Page Mode Early Write Cycle



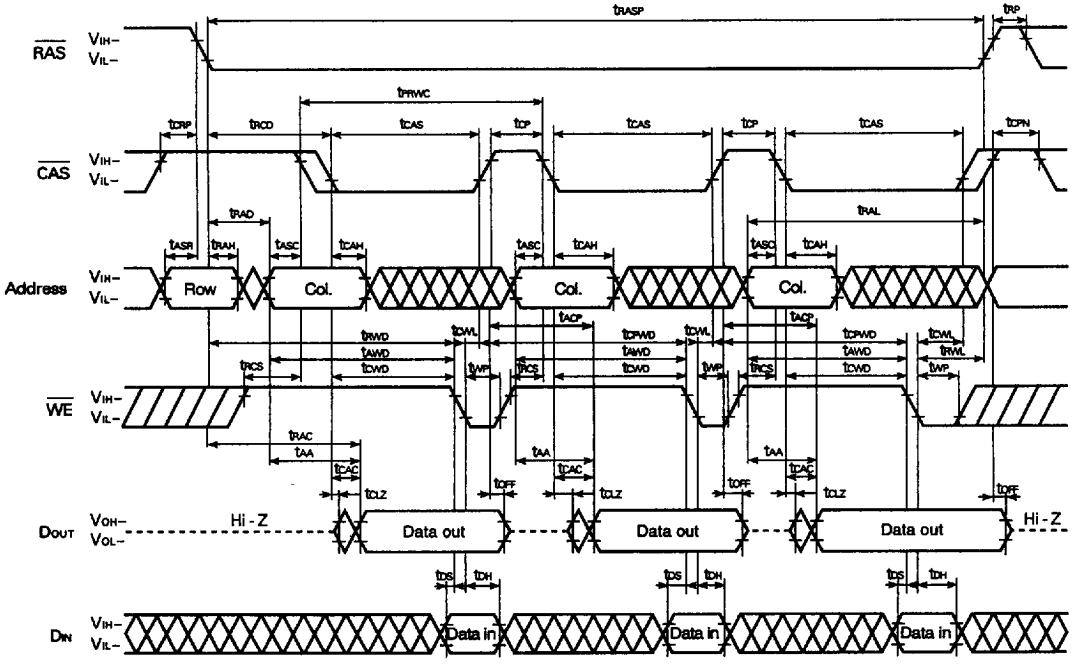
Remark In the fast page mode, read, write and read modify write cycles are available for each of the consecutive $\overline{CAS}$ cycles within the same $\overline{RAS}$ cycle.

Fast Page Mode Late Write Cycle



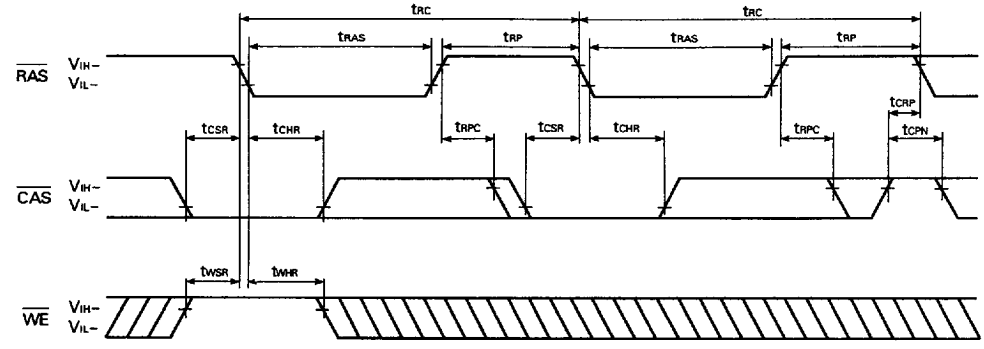
Remark In the fast page mode, read, write and read modify write cycles are available for each of the consecutive $\overline{CAS}$ cycles within the same $\overline{RAS}$ cycle.

Fast Page Mode Read Modify Write Cycle



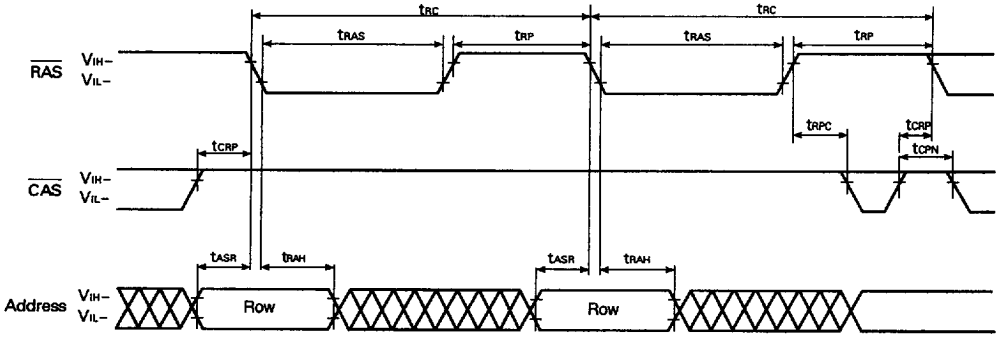
Remark In the fast page mode, read, write and read modify write cycles are available for each of the consecutive $\overline{CAS}$ cycles within the same $\overline{RAS}$ cycle.

$\overline{CAS}$ Before $\overline{RAS}$ Refresh Cycle



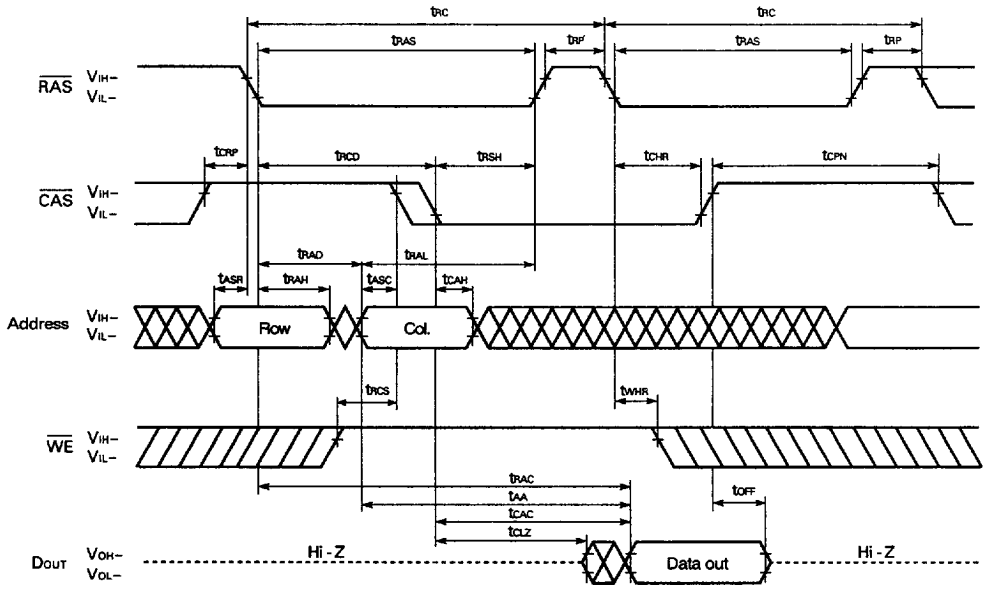
Remark Addresss, D_{IN} : Don't care D_{OUT} : Hi - Z

$\overline{RAS}$ Only Refresh Cycle



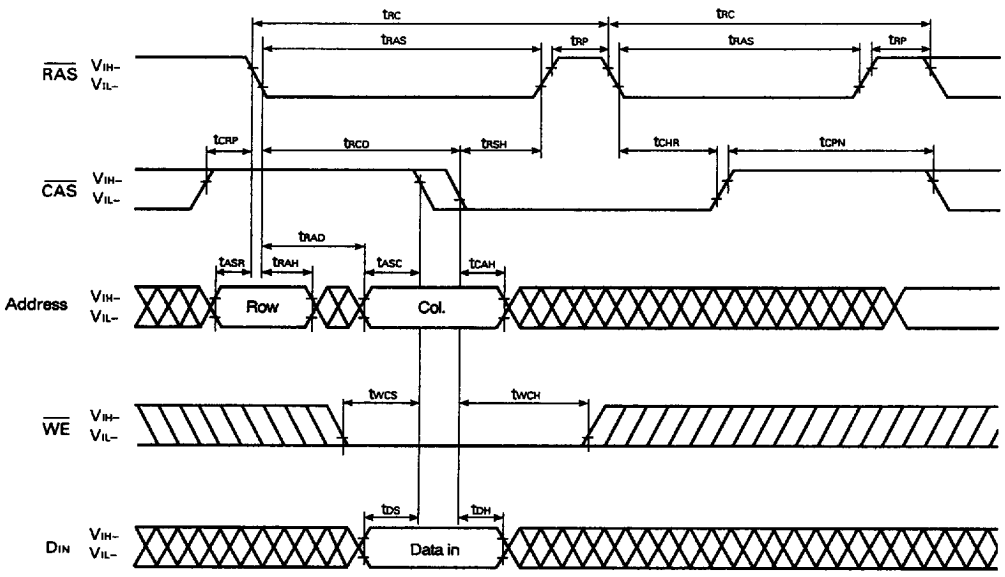
Remark $\overline{WE}$, D_{IN} : Don't care D_{OUT} : Hi - Z

Hidden Refresh Cycle (Read)



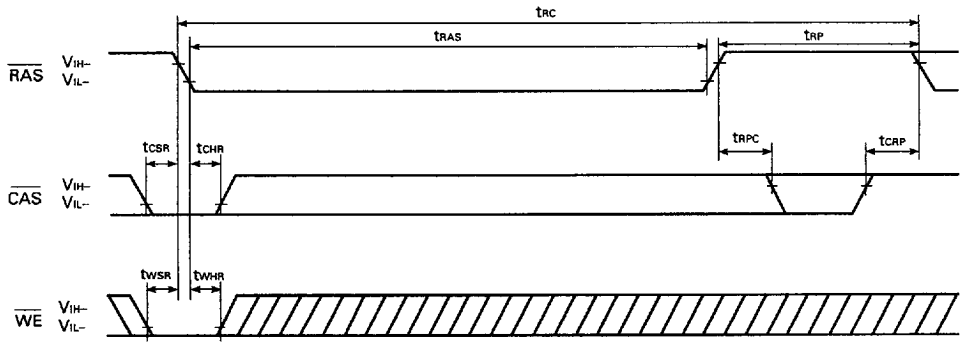
Remark D_{IN} : Don't care

Hidden Refresh Cycle (Write)



Remark DOUT : Hi-Z

Test Mode Set Cycle (WE, CAS Before RAS Refresh Cycle)



Remark Address, DIN : Don't care DOUT : Hi - Z

Test Mode

By using the test mode, the test time can be reduced. The reason for this is that, the memory emulates the × 16-bit structure during test mode.

(1) Setting the mode

Executing the test mode cycle (WE, CAS before RAS refresh cycle) sets the test mode.

(2) Write/read operation

When either a "0" or a "1" is written to the input pin in test mode, this data is written to 16 bits of memory cell.

Next, when the data is read from the output pin at the same address, the cell can be checked.

Output = "1" : Normal write (all memory cells)
Output = "0" : Abnormal write

(3) Refresh

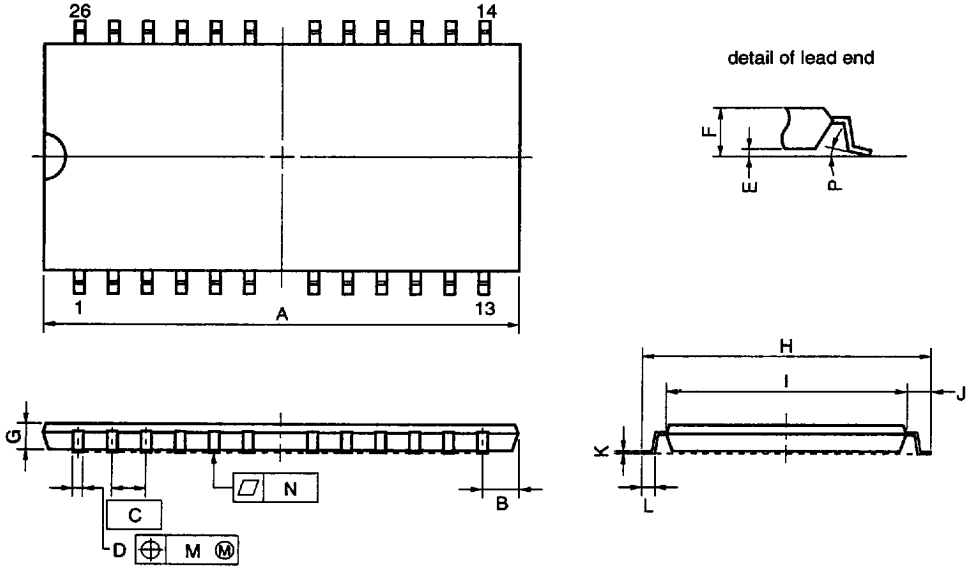
Refresh in the test mode must be performed with the RAS / CAS cycle or with the WE, CAS before RAS refresh cycle. The WE, CAS before RAS refresh cycle use the same counter as the CAS before RAS refresh's internal counter.

(4) Mode Cancellation

The test mode is cancelled by executing one cycle of RAS only refresh cycle or CAS before RAS refresh cycle.

Package Drawings

26PIN PLASTIC TSOP(II) (300 mil)



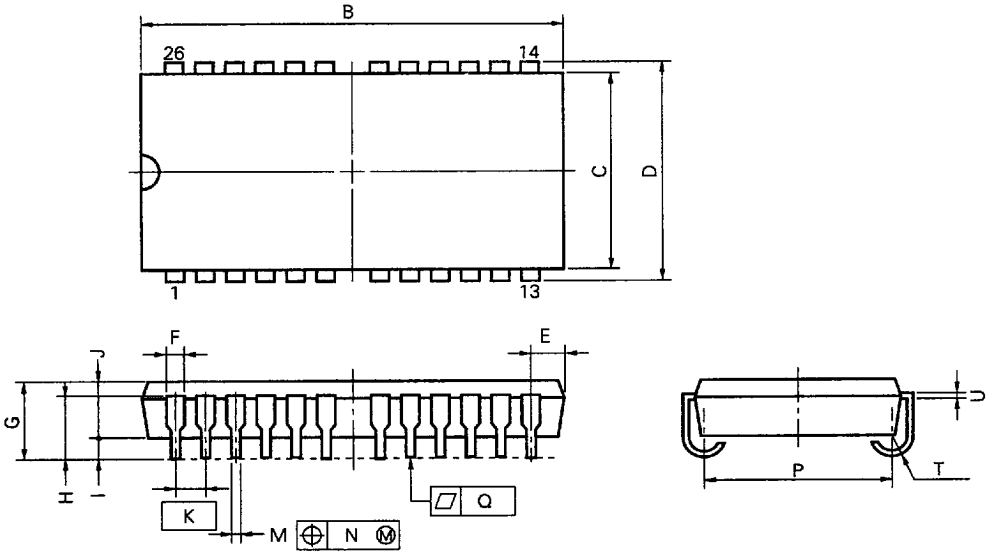
NOTE

Each lead centerline is located within 0.21 mm (0.009 inch) of its true position (T.P.) at maximum material condition.

ITEM	MILLIMETERS	INCHES
A	17.36 MAX.	0.684 MAX.
B	1.06 MAX.	0.042 MAX.
C	1.27 (T.P.)	0.050 (T.P.)
D	$0.42^{+0.08}_{-0.07}$	0.017±0.003
E	0.1±0.05	0.004±0.002
F	1.2 MAX.	0.048 MAX.
G	0.97	0.038
H	9.22±0.2	0.363±0.008
I	7.62±0.1	0.300±0.004
J	0.8±0.2	$0.031^{+0.009}_{-0.008}$
K	$0.145^{+0.025}_{-0.015}$	0.006±0.001
L	0.5±0.1	$0.020^{+0.004}_{-0.005}$
M	0.21	0.009
N	0.10	0.004
P	$3°^{+7°}_{-3°}$	$3°^{+7°}_{-3°}$

S26G3-50-7JD1

26 PIN PLASTIC SOJ (300 mil)



S26LA-300A

NOTE

Each lead centerline is located within 0.12 mm (0.005 inch) of its true position (T.P.) at maximum material condition.

ITEM	MILLIMETERS	INCHES
B	$17.1^{+0.25}_{-0.05}$	$0.673^{+0.010}_{-0.002}$
C	7.62	0.300
D	8.47±0.2	$0.333^{+0.009}_{-0.008}$
E	1.03±0.15	$0.041^{+0.006}_{-0.007}$
F	0.74	0.029
G	3.5±0.2	0.138±0.008
H	2.545±0.2	0.100±0.008
I	0.8 MIN.	0.031 MIN.
J	2.6	0.102
K	1.27 (T.P.)	0.050 (T.P.)
M	0.40±0.10	$0.016^{+0.004}_{-0.005}$
N	0.12	0.005
P	6.73±0.20	0.265±0.008
Q	0.10	0.004
T	R 0.85	R 0.033
U	$0.20^{+0.10}_{-0.05}$	$0.008^{+0.004}_{-0.002}$

Recommended Soldering Conditions

The following conditions (see table below) must be met for soldering conditions of the μPD4216100, 4217100.

For more details, refer to our document "SEMICONDUCTOR DEVICE MOUNTING TECHNOLOGY MANUAL" (IEI-1207).

Please consult with our sales offices in case other soldering process is used, or in case the soldering is done under different conditions.

Type of Surface Mount Device

μPD4216100G3, 4217100G3 : 26-pin Plastic TSOP (II) (300 mil)

Please consult with our sales offices.

μPD4216100LA, 4217100LA

Soldering process	Soldering conditions	Symbol
Infrared ray reflow	Peak temperature of package surface : 235 °C or below, Reflow time : 30 seconds or below (210 °C or higher), Number of reflow processes : MAX. 2 Exposure limit[Note] : 7 days (20 hours pre-baking is required at 125 °C afterwards) **[Remark]** (1) Please start the second reflow process after the temperature, raised by the first reflow process, returns to normal. (2) Please avoid removing the residual flux with water after the first reflow process.	IR35-207-2
VPS	Peak temperature of package : 215 °C or below, Reflow time : 40 seconds or below (200 °C or higher), Number of reflow processes : MAX. 2 Exposure limit[Note] : 7 days (20 hours pre-baking is required at 125 °C afterwards) **[Remark]** (1) Please start the second reflow process after the temperature, raised by the first reflow process, returns to normal. (2) Please avoid removing the residual flux with water after the first reflow process.	VP15-207-2
Partial heating method	Terminal temperature : 300 °C or below, Time : 3 seconds or below (Per one side of the device).	———

Note Exposure limit before soldering after dry-pack package is opened.
Storage conditions: 25 °C and relative humidity at 65 % or less.

Caution Do not apply more than one soldering method at any one time, except for "Partial heating method".